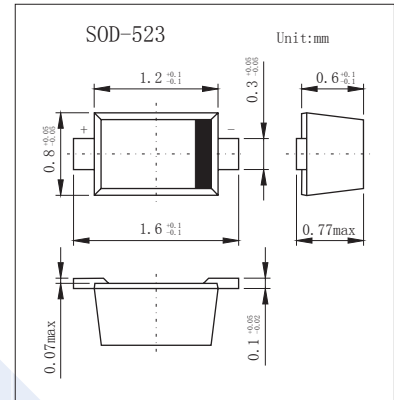


High Speed Switching Diodes

HSC119 (KSC119)

■ Features

- Low capacitance. (C = 2.0 pF max)
- Short reverse recovery time. (trr = 3.0 ns max)
- Ultra small Flat Package (UFP) is suitable for surface mount design.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Reverse voltage	V _{RM}	85	V
Forward current	I _F	100	mA
Peak forward surge current	I _{FM}	300	
Junction Temperature	T _J	125	°C
Storage temperature range	T _{stg}	-55 to 125	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V _R	I _R = 100 μ A	85			V
Forward voltage	V _{F1}	I _F = 10mA			0.8	
	V _{F2}	I _F = 100mA			1.2	
Reverse voltage leakage current	I _{R1}	V _R = 80V			0.1	μ A
Junction capacitance	C _j	V _R = 0V, f= 1 MHz			2	pF
Reverse recovery time	t _{rr}	I _F =10mA, V _R =6V, R _L =50 Ω			3	ns

■ Marking

Marking	A
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High Speed Switching Diodes

HSC119 (KSC119)

■ Typical Characteristics

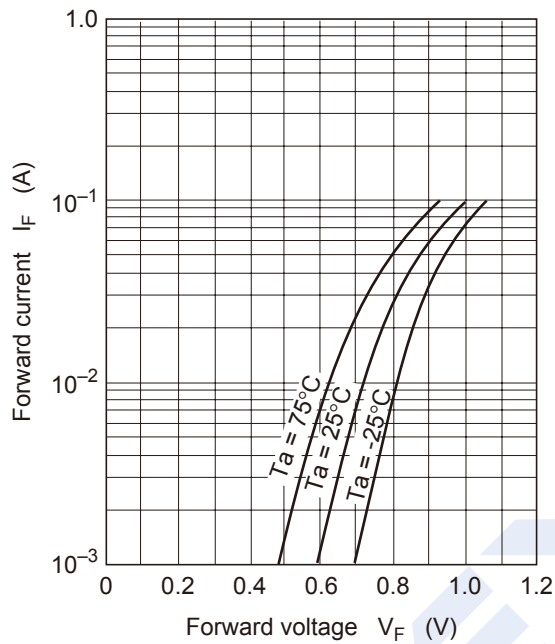


Fig.1 Forward current vs. Forward voltage

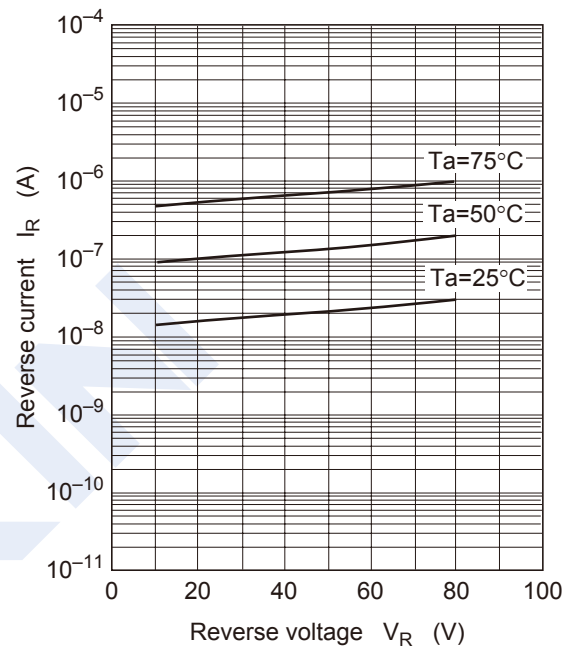


Fig.2 Reverse current vs. Reverse voltage

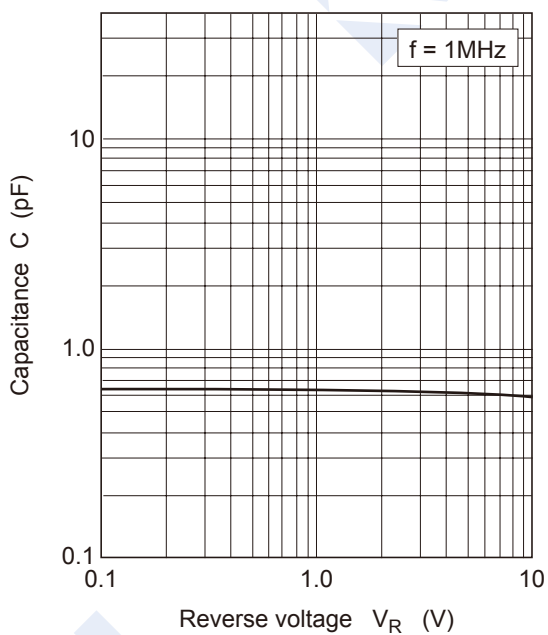


Fig.3 Capacitance vs. Reverse voltage

